

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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061282-0234

 SERIAL NO.
10/574,863

 APPLICANT
Yuichiro SASAKI, et al.

 FILING DATE
April 06, 2006

 GROUP
2823

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
		International Search Report issued in International Patent Application No. PCT/JP2005/009949 dated July 5, 2005
		International Search Report issued in International Patent Application No. PCT/JP2004015308 mailed January 18, 2005
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1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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